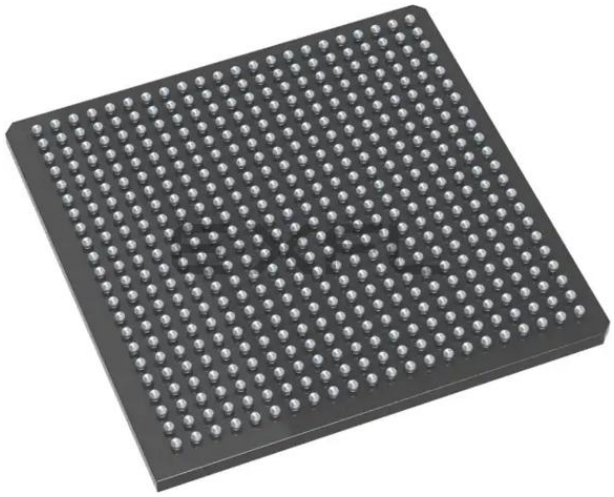


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

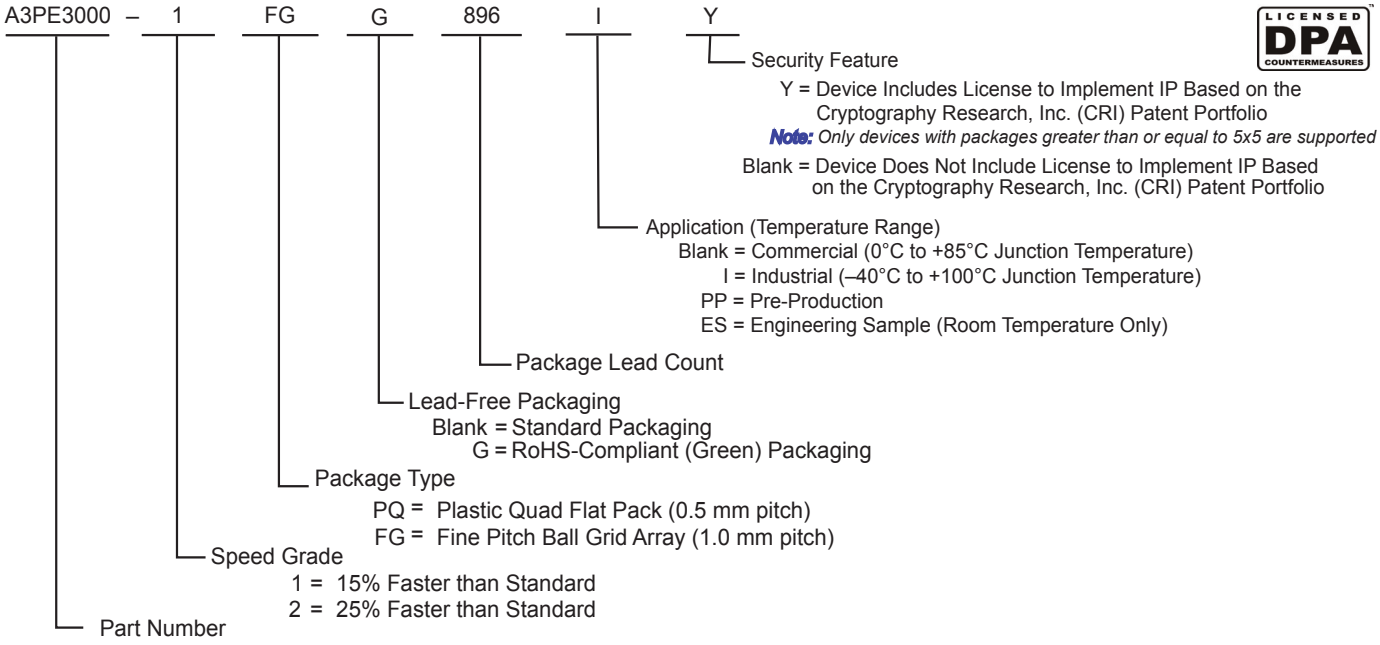
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	280
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe1500-fg484i

ProASIC3E Ordering Information



ProASIC3E Devices

A3PE600 = 600,000 System Gates
A3PE1500 = 1,500,000 System Gates
A3PE3000 = 3,000,000 System Gates

ProASIC3E Devices with Cortex-M1

M1A3PE1500 = 1,500,000 System Gates
M1A3PE3000 = 3,000,000 System Gates

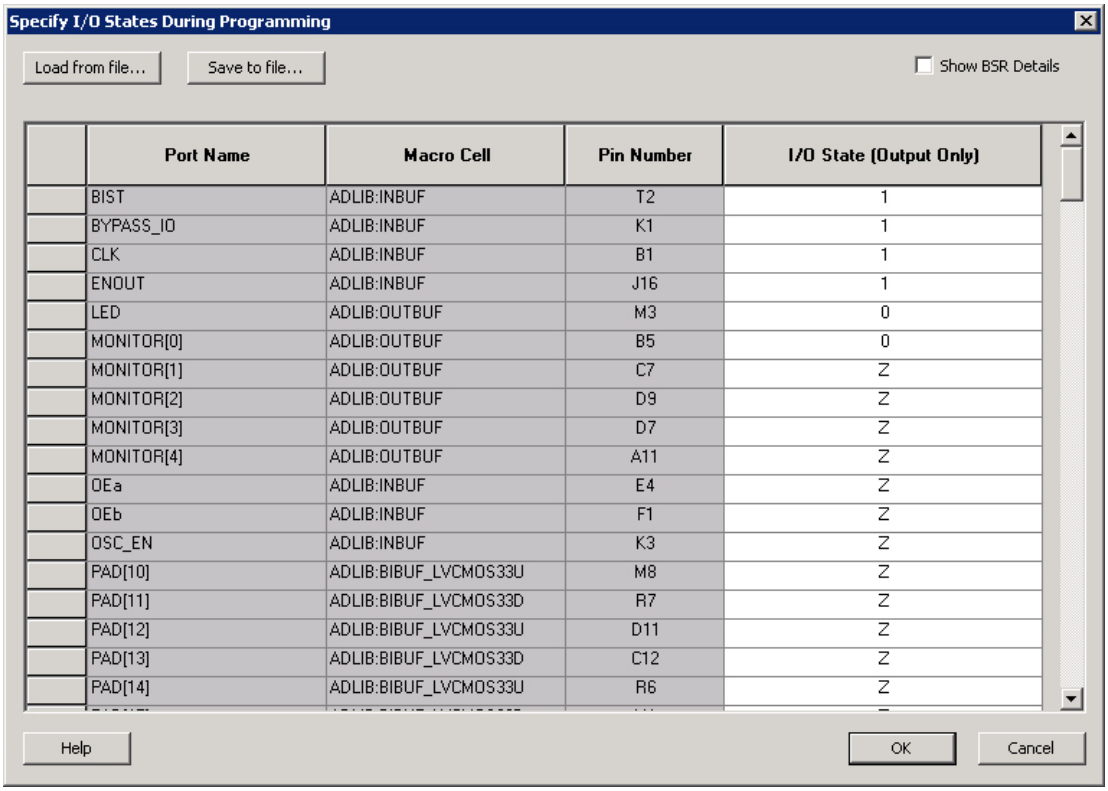


Figure 1-3 • **I/O States During Programming Window**

6. Click OK to return to the FlashPoint – Programming File Generator window.

   I/O States during programming are saved to the ADB and resulting programming files after completing programming file generation.

Table 2-8 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings (continued)

	VMV (V)	Static Power PDC2 (mW)[1]	Dynamic Power PAC9 (µW/MHz)[2]
HSTL (I)	1.5	0.17	2.03
HSTL (II)	1.5	0.17	2.03
SSTL2 (I)	2.5	1.38	4.48
SSTL2 (II)	2.5	1.38	4.48
SSTL3 (I)	3.3	3.21	9.26
SSTL3 (II)	3.3	3.21	9.26
Differential			
LVDS/B-LVDS/M-LVDS	2.5	2.26	1.50
LVPECL	3.3	5.71	2.17

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.*

Table 2-9 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings [1]

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL/LVCMOS	35	3.3	–	474.70
3.3 V LVTTL/LVCMOS Wide Range[4]	35	3.3	–	474.70
2.5 V LVCMOS	35	2.5	–	270.73
1.8 V LVCMOS	35	1.8	–	151.78
1.5 V LVCMOS (JESD8-11)	35	1.5	–	104.55
3.3 V PCI	10	3.3	–	204.61
3.3 V PCI-X	10	3.3	–	204.61
Voltage-Referenced				
3.3 V GTL	10	3.3	–	24.08
2.5 V GTL	10	2.5	–	13.52
3.3 V GTL+	10	3.3	–	24.10
2.5 V GTL+	10	2.5	–	13.54
HSTL (I)	20	1.5	7.08	26.22
HSTL (II)	20	1.5	13.88	27.22
SSTL2 (I)	30	2.5	16.69	105.56
SSTL2 (II)	30	2.5	25.91	116.60

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC3 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-21 • I/O Short Currents IOSH/IOSL

	Drive Strength	IOSH (mA)*	IOSL (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	4 mA	16	18
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55

Notes:

1. *T_J = 100°C*
2. *Applicable to 3.3 V LVCMOS Wide Range. IOSL/IOSH dependent on the I/O buffer drive strength selected for wide range applications. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.*

The length of time an I/O can withstand IOSH/IOSL events depends on the junction temperature. The reliability data below is based on a 3.3 V, 36 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C, the short current condition would have to be sustained for more than six months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-22 • Duration of Short Circuit Event Before Failure

Temperature	Time before Failure
–40°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years

3.3 V LVCMOS Wide Range

Table 2-29 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	109	103	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	127	132	10	10
100 µA	24 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	181	268	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

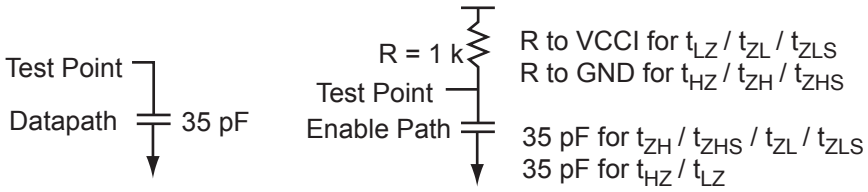


Figure 2-7 • AC Loading

Table 2-30 • 3.3 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	1.4	–	35

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

SSTL2 Class I

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). ProASIC3E devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-66 • Minimum and Maximum DC Input and Output Levels

SSTL2 Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
15 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.54	VCCI – 0.62	15	15	87	83	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

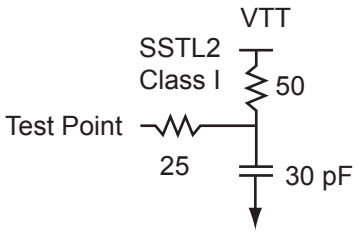


Figure 2-18 • AC Loading

Table 2-67 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.25	1.25	1.25	30

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-68 • SSTL 2 Class I
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	2.13	0.04	1.33	0.43	2.17	1.85			4.40	4.08	ns
–1	0.56	1.81	0.04	1.14	0.36	1.84	1.57			3.74	3.47	ns
–2	0.49	1.59	0.03	1.00	0.32	1.62	1.38			3.29	3.05	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

***Table 2-85* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-26 on page 2-55 for more information.*

Input Register

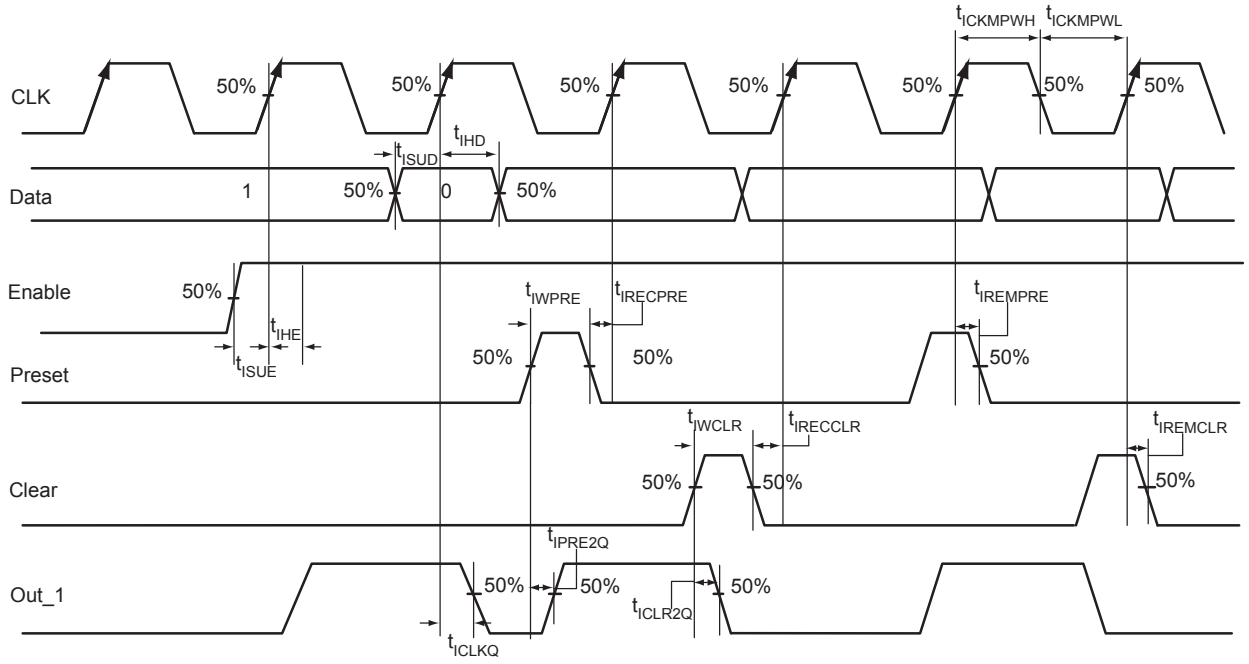


Figure 2-27 • **Input Register Timing Diagram**

Timing Characteristics

Table 2-86 • **Input Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.24	0.27	0.32	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.26	0.30	0.35	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.37	0.42	0.50	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.45	0.52	0.61	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.41	0.48	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Output DDR Module

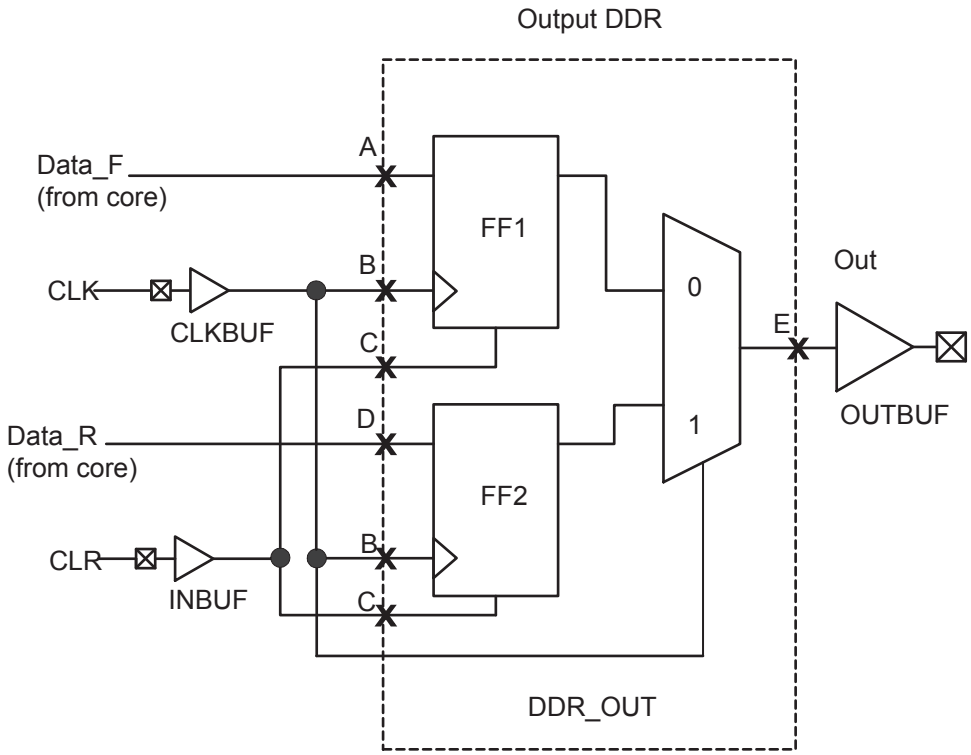


Figure 2-32 • **Output DDR Timing Model**

Table 2-91 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

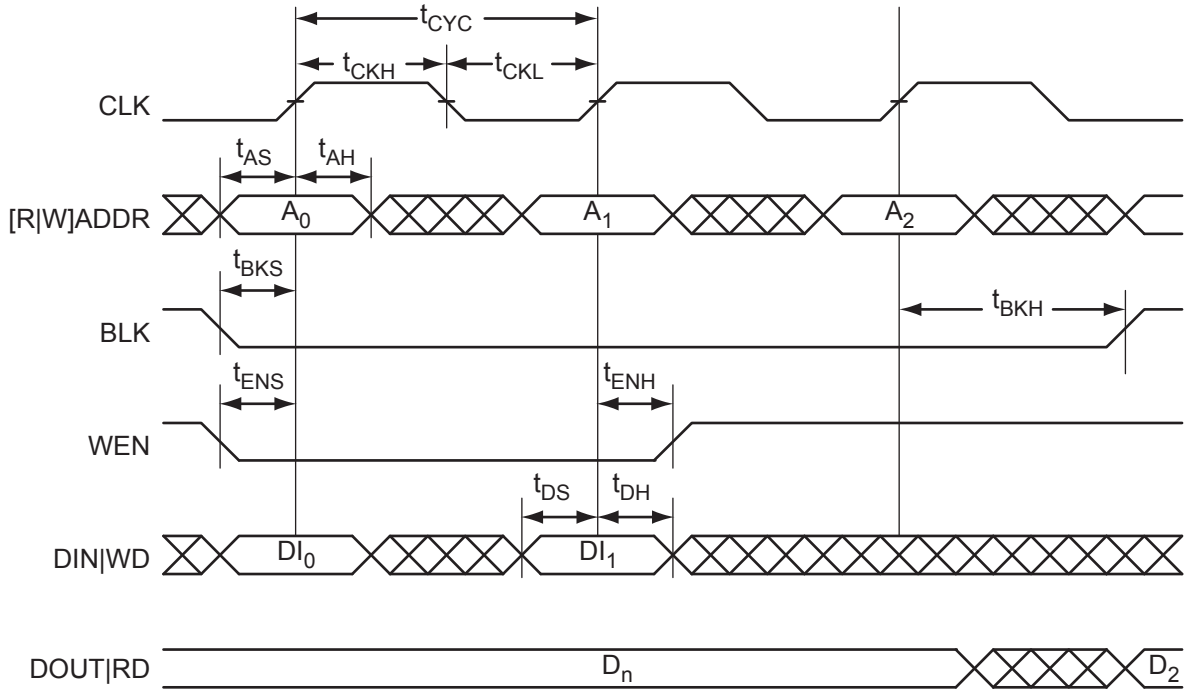


Figure 2-43 • **RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**

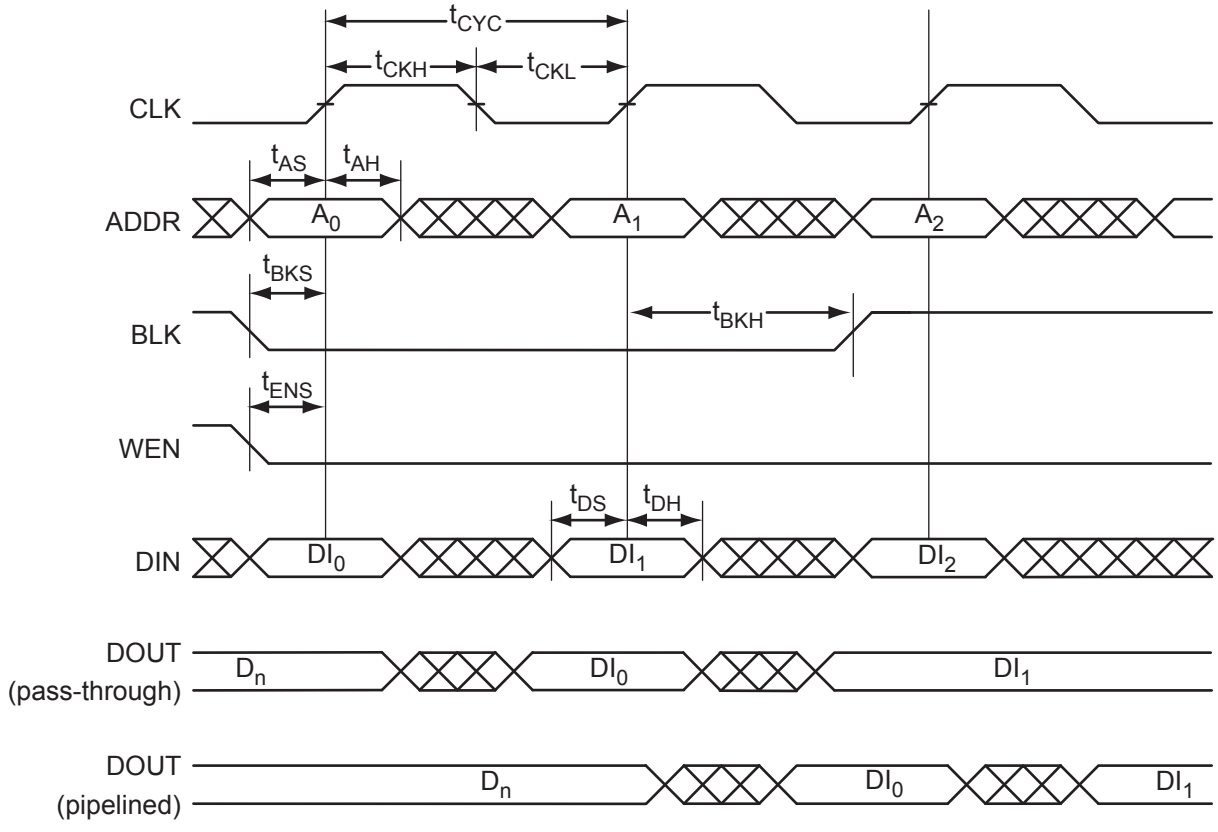


Figure 2-44 • **RAM Write, Output as Write Data. Applicable to RAM4K9 Only.**

Timing Characteristics

Table 2-99 • RAM4K9
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BLK hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.79	2.03	2.39	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWL} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t_{C2CWWH} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DO (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Timing Characteristics

Table 2-101 • FIFO
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.38	1.57	1.84	ns
t_{ENH}	REN, WEN Hold Time	0.02	0.02	0.02	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (pass-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (pass-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET Removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET Recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency	310	272	231	MHz

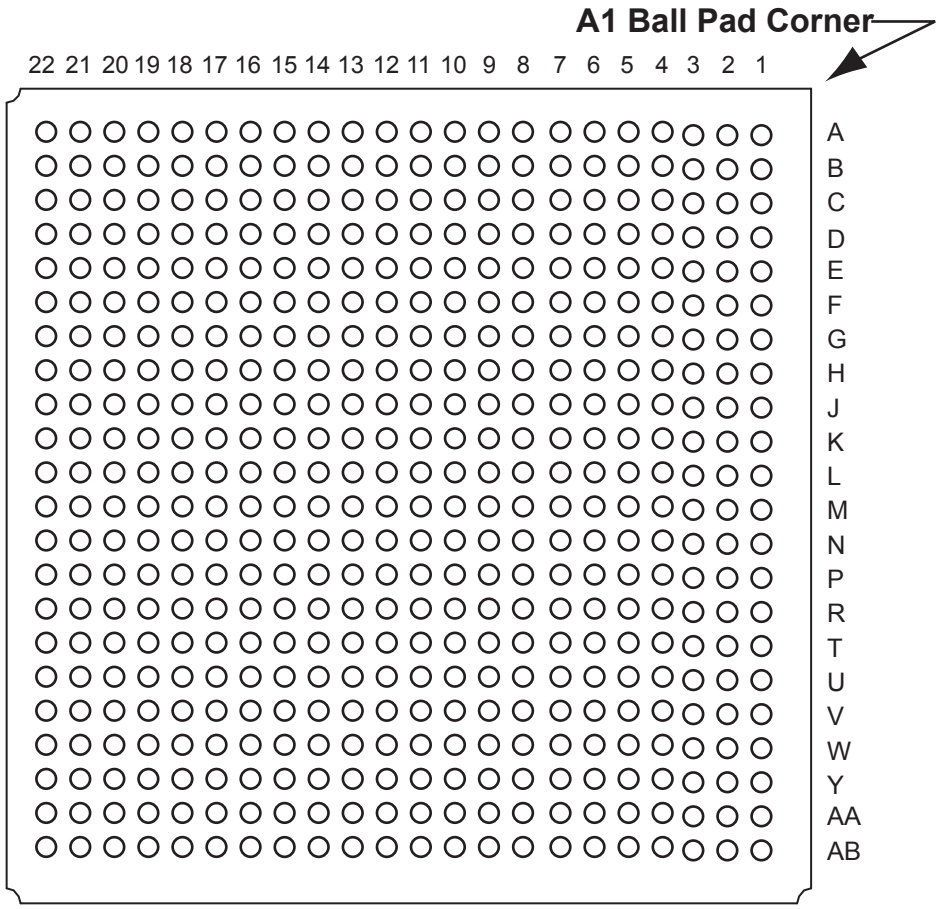
Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

FG324	
Pin Number	A3PE3000 FBGA
G1	GND
G2	IO287PDB7V1
G3	IO287NDB7V1
G4	IO283PPB7V1
G5	VCCIB7
G6	IO279PDB7V0
G7	IO291NPB7V2
G8	VCC
G9	IO26NDB0V3
G10	IO34NDB0V4
G11	VCC
G12	IO94NPB2V1
G13	IO98PDB2V2
G14	VCCIB2
G15	GCC0/IO112NPB2V3
G16	IO104PDB2V2
G17	IO104NDB2V2
G18	GND
H1	IO267PDB6V4
H2	VCCIB7
H3	IO283NPB7V1
H4	GFB1/IO274PPB7V0
H5	GND
H6	IO279NDB7V0
H7	VCC
H8	VCC
H9	GND
H10	GND
H11	VCC
H12	VCC
H13	IO98NDB2V2
H14	GND
H15	GCB1/IO113PDB2V3
H16	GCC1/IO112PPB2V3
H17	VCCIB2
H18	IO108PDB2V3

FG324	
Pin Number	A3PE3000 FBGA
J1	IO267NDB6V4
J2	GFA0/IO273NDB6V4
J3	VCOMPLF
J4	GFA2/IO272PDB6V4
J5	GFB0/IO274NPB7V0
J6	GFC0/IO275NDB7V0
J7	GFC1/IO275PDB7V0
J8	GND
J9	GND
J10	GND
J11	GND
J12	GCA2/IO115PDB3V0
J13	GCA1/IO114PDB3V0
J14	GCA0/IO114NDB3V0
J15	GCB0/IO113NDB2V3
J16	VCOMPLC
J17	IO120NPB3V0
J18	IO108NDB2V3
K1	IO263PDB6V3
K2	GFA1/IO273PDB6V4
K3	VCCPLF
K4	IO272NDB6V4
K5	GFC2/IO270PPB6V4
K6	GFB2/IO271PDB6V4
K7	IO271NDB6V4
K8	GND
K9	GND
K10	GND
K11	GND
K12	IO115NDB3V0
K13	GCB2/IO116PDB3V0
K14	IO116NDB3V0
K15	GCC2/IO117PDB3V0
K16	VCCPLC
K17	IO124NPB3V1
K18	IO120PPB3V0

FG324	
Pin Number	A3PE3000 FBGA
L1	IO263NDB6V3
L2	VCCIB6
L3	IO259PDB6V3
L4	IO259NDB6V3
L5	GND
L6	IO270NPB6V4
L7	VCC
L8	VCC
L9	GND
L10	GND
L11	VCC
L12	VCC
L13	IO132PDB3V2
L14	GND
L15	IO117NDB3V0
L16	IO128NPB3V1
L17	VCCIB3
L18	IO124PPB3V1
M1	GND
M2	IO255PDB6V2
M3	IO255NDB6V2
M4	IO251PPB6V2
M5	VCCIB6
M6	GEB0/IO235NDB6V0
M7	GEB1/IO235PDB6V0
M8	VCC
M9	IO192PPB4V4
M10	IO154NPB4V0
M11	VCC
M12	GDA0/IO153NPB3V4
M13	IO132NDB3V2
M14	VCCIB3
M15	IO134NDB3V2
M16	IO134PDB3V2
M17	IO128PPB3V1
M18	GND

FG484



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	**A3PE3000 Function**
C21	IO94PPB2V1
C22	VCCIB2
D1	IO293PDB7V2
D2	IO303NDB7V3
D3	IO305NDB7V3
D4	GND
D5	GAA0/IO00NDB0V0
D6	GAA1/IO00PDB0V0
D7	GAB0/IO01NDB0V0
D8	IO20PDB0V2
D9	IO22PDB0V2
D10	IO30PDB0V3
D11	IO38NDB0V4
D12	IO52NDB1V1
D13	IO52PDB1V1
D14	IO66NDB1V3
D15	IO66PDB1V3
D16	GBB1/IO80PDB1V4
D17	GBA0/IO81NDB1V4
D18	GBA1/IO81PDB1V4
D19	GND
D20	IO88PDB2V0
D21	IO90PDB2V1
D22	IO94NPB2V1
E1	IO293NDB7V2
E2	IO299PPB7V3
E3	GND
E4	GAB2/IO308PDB7V4
E5	GAA2/IO309PDB7V4
E6	GNDQ
E7	GAB1/IO01PDB0V0
E8	IO20NDB0V2
E9	IO22NDB0V2
E10	IO30NDB0V3
E11	IO38PDB0V4
E12	IO44NDB1V0

FG484	
Pin Number	**A3PE3000 Function**
E13	IO58NDB1V2
E14	IO58PDB1V2
E15	GBC1/IO79PDB1V4
E16	GBB0/IO80NDB1V4
E17	GNDQ
E18	GBA2/IO82PDB2V0
E19	IO86NDB2V0
E20	GND
E21	IO90NDB2V1
E22	IO98PDB2V2
F1	IO299NPB7V3
F2	IO301NDB7V3
F3	IO301PDB7V3
F4	IO308NDB7V4
F5	IO309NDB7V4
F6	VMV7
F7	VCCPLA
F8	GAC0/IO02NDB0V0
F9	GAC1/IO02PDB0V0
F10	IO32NDB0V3
F11	IO32PDB0V3
F12	IO44PDB1V0
F13	IO50NDB1V1
F14	IO60PDB1V2
F15	GBC0/IO79NDB1V4
F16	VCCPLB
F17	VMV2
F18	IO82NDB2V0
F19	IO86PDB2V0
F20	IO96PDB2V1
F21	IO96NDB2V1
F22	IO98NDB2V2
G1	IO289NDB7V1
G2	IO289PDB7V1
G3	IO291PPB7V2
G4	IO295PDB7V2

FG484	
Pin Number	**A3PE3000 Function**
G5	IO297PDB7V2
G6	GAC2/IO307PDB7V4
G7	VCOMPLA
G8	GNDQ
G9	IO26NDB0V3
G10	IO26PDB0V3
G11	IO36PDB0V4
G12	IO42PDB1V0
G13	IO50PDB1V1
G14	IO60NDB1V2
G15	GNDQ
G16	VCOMPLB
G17	GBB2/IO83PDB2V0
G18	IO92PDB2V1
G19	IO92NDB2V1
G20	IO102PDB2V2
G21	IO102NDB2V2
G22	IO105NDB2V2
H1	IO286PSB7V1
H2	IO291NPB7V2
H3	VCC
H4	IO295NDB7V2
H5	IO297NDB7V2
H6	IO307NDB7V4
H7	IO287PDB7V1
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO36NDB0V4
H12	IO42NDB1V0
H13	VCCIB1
H14	VCCIB1
H15	VMV1
H16	GBC2/IO84PDB2V0
H17	IO83NDB2V0
H18	IO100NDB2V2

FG676	
Pin Number	A3PE1500 Function
A1	GND
A2	GND
A3	GAA0/IO00NDB0V0
A4	GAA1/IO00PDB0V0
A5	IO06NDB0V0
A6	IO09NDB0V1
A7	IO09PDB0V1
A8	IO14NDB0V1
A9	IO14PDB0V1
A10	IO22NDB0V2
A11	IO22PDB0V2
A12	IO26NDB0V3
A13	IO26PDB0V3
A14	IO30NDB0V3
A15	IO30PDB0V3
A16	IO34NDB1V0
A17	IO34PDB1V0
A18	IO38NDB1V0
A19	IO38PDB1V0
A20	IO41PDB1V1
A21	IO44PDB1V1
A22	IO49PDB1V2
A23	IO50PDB1V2
A24	GBC1/IO55PDB1V3
A25	GND
A26	GND
AA1	IO174PDB6V0
AA2	IO171PDB6V0
AA3	GEA1/IO167PPB6V0
AA4	GEC0/IO169NPB6V0
AA5	VCOMPLE
AA6	GND
AA7	IO165NDB5V3
AA8	GEB2/IO165PDB5V3
AA9	IO163PDB5V3
AA10	IO159NDB5V3

FG676	
Pin Number	A3PE1500 Function
AA11	IO153NDB5V2
AA12	IO147NDB5V1
AA13	IO139NDB5V0
AA14	IO137NDB5V0
AA15	IO123NDB4V1
AA16	IO123PDB4V1
AA17	IO117NDB4V0
AA18	IO117PDB4V0
AA19	GDB2/IO112PDB4V0
AA20	GNDQ
AA21	TDO
AA22	GND
AA23	GND
AA24	IO102NDB3V1
AA25	IO102PDB3V1
AA26	IO98NDB3V1
AB1	IO174NDB6V0
AB2	IO171NDB6V0
AB3	GEB1/IO168PPB6V0
AB4	GEA0/IO167NPB6V0
AB5	VCCPLE
AB6	GND
AB7	GND
AB8	IO156NDB5V2
AB9	IO156PDB5V2
AB10	IO150PDB5V1
AB11	IO155PDB5V2
AB12	IO142PDB5V0
AB13	IO135NDB5V0
AB14	IO135PDB5V0
AB15	IO132PDB4V2
AB16	IO129PDB4V2
AB17	IO121PDB4V1
AB18	IO119NDB4V1
AB19	IO112NDB4V0
AB20	VMV4

FG676	
Pin Number	A3PE1500 Function
AB21	TCK
AB22	TRST
AB23	GDC0/IO108NDB3V2
AB24	GDC1/IO108PDB3V2
AB25	IO104NDB3V2
AB26	IO104PDB3V2
AC1	IO170PDB6V0
AC2	GEB0/IO168NPB6V0
AC3	IO166NPB5V3
AC4	GNDQ
AC5	GND
AC6	IO160PDB5V3
AC7	IO161PDB5V3
AC8	IO154PDB5V2
AC9	GND
AC10	IO150NDB5V1
AC11	IO155NDB5V2
AC12	IO142NDB5V0
AC13	IO138NDB5V0
AC14	IO138PDB5V0
AC15	IO132NDB4V2
AC16	IO129NDB4V2
AC17	IO121NDB4V1
AC18	IO119PDB4V1
AC19	IO118NDB4V0
AC20	IO118PDB4V0
AC21	IO114PPB4V0
AC22	TMS
AC23	VJTAG
AC24	VMV3
AC25	IO106NDB3V2
AC26	IO106PDB3V2
AD1	IO170NDB6V0
AD2	GEA2/IO166PPB5V3
AD3	VMV5
AD4	GEC2/IO164PDB5V3

FG896	
Pin Number	A3PE3000 Function
J5	IO295NDB7V2
J6	IO299NDB7V3
J7	VCCIB7
J8	VCCPLA
J9	VCC
J10	IO04NPB0V0
J11	IO18NDB0V2
J12	IO20NDB0V2
J13	IO20PDB0V2
J14	IO32NDB0V3
J15	IO32PDB0V3
J16	IO42PDB1V0
J17	IO44NDB1V0
J18	IO44PDB1V0
J19	IO54NDB1V1
J20	IO54PDB1V1
J21	IO76NPB1V4
J22	VCC
J23	VCCPLB
J24	VCCIB2
J25	IO90PDB2V1
J26	IO90NDB2V1
J27	GBB2/IO83PDB2V0
J28	IO83NDB2V0
J29	IO91PDB2V1
J30	IO91NDB2V1
K1	IO288NDB7V1
K2	IO288PDB7V1
K3	IO304NDB7V3
K4	IO304PDB7V3
K5	GAB2/IO308PDB7V4
K6	IO308NDB7V4
K7	IO301PDB7V3
K8	IO301NDB7V3
K9	GAC2/IO307PPB7V4
K10	VCC

FG896	
Pin Number	A3PE3000 Function
K11	IO04PPB0V0
K12	VCCIB0
K13	VCCIB0
K14	VCCIB0
K15	VCCIB0
K16	VCCIB1
K17	VCCIB1
K18	VCCIB1
K19	VCCIB1
K20	IO76PPB1V4
K21	VCC
K22	IO78PPB1V4
K23	IO88NDB2V0
K24	IO88PDB2V0
K25	IO94PDB2V1
K26	IO94NDB2V1
K27	IO85PDB2V0
K28	IO85NDB2V0
K29	IO93PDB2V1
K30	IO93NDB2V1
L1	IO286NDB7V1
L2	IO286PDB7V1
L3	IO298NDB7V3
L4	IO298PDB7V3
L5	IO283PDB7V1
L6	IO291NDB7V2
L7	IO291PDB7V2
L8	IO293PDB7V2
L9	IO293NDB7V2
L10	IO307NPB7V4
L11	VCC
L12	VCC
L13	VCC
L14	VCC
L15	VCC
L16	VCC

FG896	
Pin Number	A3PE3000 Function
L17	VCC
L18	VCC
L19	VCC
L20	VCC
L21	IO78NPB1V4
L22	IO104NPB2V2
L23	IO98NDB2V2
L24	IO98PDB2V2
L25	IO87PDB2V0
L26	IO87NDB2V0
L27	IO97PDB2V1
L28	IO101PDB2V2
L29	IO103PDB2V2
L30	IO119NDB3V0
M1	IO282NDB7V1
M2	IO282PDB7V1
M3	IO292NDB7V2
M4	IO292PDB7V2
M5	IO283NDB7V1
M6	IO285PDB7V1
M7	IO287PDB7V1
M8	IO289PDB7V1
M9	IO289NDB7V1
M10	VCCIB7
M11	VCC
M12	GND
M13	GND
M14	GND
M15	GND
M16	GND
M17	GND
M18	GND
M19	GND
M20	VCC
M21	VCCIB2
M22	NC

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-19 • I/O Output Buffer Maximum Resistances[1] and Table 2-21 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33853). 3.3 V LVCMOS Wide Range information was separated from regular 3.3 V LVCMOS and placed into its own new section, "3.3 V LVCMOS Wide Range". Values of IOSH and IOSL were added in Table 2-29 • Minimum and Maximum DC Input and Output Levels (SAR 33853).	2-20, 2-27
	The formulas in the table notes for Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34755).	2-21
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34889).	2-24
	The titles and subtitles for Table 2-31 • 3.3 V LVCMOS Wide Range High Slew and Table 2-32 • 3.3 V LVCMOS Wide Range Low Slew were corrected (SAR 37227).	2-28, 2-29
	The following notes were removed from Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 34812): ±5% Differential input voltage = ±350 mV	2-50
	Minimum pulse width High and Low values were added to the tables in the "Global Tree Timing Characteristics" section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36957).	2-68
	A note was added to Table 2-98 • ProASIC3E CCC/PLL Specification indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34824).	2-70
	The following figures were deleted. Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 34872). Figure 2-44 • Write Access after Write onto Same Address Figure 2-45 • Read Access after Write onto Same Address Figure 2-46 • Write Access after Read onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-49 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35750).	2-74, 2-75, 2-79, 2-82
	The "Pin Descriptions and Packaging" chapter is new (SAR 34771).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 34771).	4-1
	Pin E6 for the FG256 package was corrected from VvB0 to VCCIB0 (SARs 30364, 31597, 26243).	4-9
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3E Device Status" table on page II indicates the status for each device in the device family.	N/A

Revision	Changes	Page
v2.0 (continued)	Table 3-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	3-5
	Table 3-5 • Package Thermal Resistivities was updated.	3-5
	Table 3-10 • Different Components Contributing to the Dynamic Power Consumption in ProASIC3E Devices was updated.	3-8
	t_{WRO} and t_{CCKH} were added to Table 3-94 • RAM4K9 and Table 3-95 • RAM512X18.	3-74 to 3-74
	The note in Table 3-24 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-23
	Figure 3-43 • Write Access After Write onto Same Address, Figure 3-44 • Read Access After Write onto Same Address, and Figure 3-45 • Write Access After Read onto Same Address are new.	3-71 to 3-73
	Figure 3-53 • Timing Diagram was updated.	3-80
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3PE1500 "208-Pin PQFP" table is new.	4-4
	The A3PE1500 "484-Pin FBGA" table is new.	4-18
	The A3PE1500 "A3PE1500 Function" table is new.	4-24
Advance v0.6 (January 2007)	In the "Packaging Tables" table, the number of I/Os for the A3PE1500 was changed for the FG484 and FG676 packages.	ii
Advance v0.5 (April 2006)	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-8 • Very-Long-Line Resources was updated.	2-8
	The footnotes in Figure 2-27 • CCC/PLL Macro were updated.	2-28
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21
	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-8 • Very-Long-Line Resources was updated.	2-8
	The footnotes in Figure 2-27 • CCC/PLL Macro were updated.	2-28
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21
	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "ProASIC3E Device Status" table on page II, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

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